

LESD5D5.0CT1G

Transient Voltage Suppressors for ESD protection

DESCRIPTION

The LESD5D5.0CT1G is designed to protect voltage sensitive components from ESD and transient voltage events. Excellent clamping capability, low leakage, and fast response time, make these parts ideal for ESD protection on designs where board space is at a premium.

This device has been specifically designed to protect sensitive components which are connected to data and transmission lines from overvoltage caused by ESD (electrostatic discharge), CDE (Cable Discharge Events), and EFT (electrical fast transients).

FEATURES

- ♦IEC61000-4-2 (ESD) ±15kV (air), ±8kV (contact)
- ♦IEC61000-4-4 (EFT) 40A (5/50ηs)
- ♦ Peak power dissipation: 75W (8/20µs)
- ♦Protects one I/O line
- ♦Low clamping voltage
- ♦Working voltages : 5V
- ♦Low leakage current

MACHANICAL DATA

- ♦SOD-523 package
- ♦ Packaging: Tape and Reel
- ♦Reel size: 7 inch
- ♦MSL3

ORDERING INFORMATION

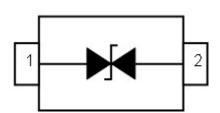
Device: LESD5D5.0CT1G
 Package: SOD-523
 Material: Halogen free
 Packing: Tape & Reel

♦ Quantity per reel: 3,000pcs

APPLICATIONS

- ♦ High Speed Line: USB1.0/2.0, VGA, DVI, SDI,
- ♦ Serial and Parallel Ports
- ♦ Notebooks, Desktops, Servers
- ♦ Projection TV
- ♦ Cellular handsets and accessories
- ♦ Portable instrumentation
- ♦Peripherals

PIN CONFIGURATION



PACKAGE OUTLINE





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ABSOLUTE MAXIMUM RATING							
Symbol	ymbol Parameter		Units				
V _{ESD}	ESD per IEC 61000-4-2 (Air) ESD per IEC 61000-4-2 (Contact)	±30 ±30	kV				
P _{PP}	Peak Pulse Power (8/20µs)	75	W				
T _{OPT}	Operating Temperature	-40~150	°C				
T _{STG}	Storage Temperature	-40~150	°C				

ELECTRICAL CHARACTERISTICS (Tamb=25°C)								
Symbol	Parameter	Test Condition	Min	Тур	Max	Units		
V_{RWM}	Reverse Working Voltage				5.0	V		
V_{BR}	Reverse Breakdown Voltage	I _T = 1mA	5.6		9.0	V		
I _R	Reverse Leakage Current	V _{RWM} = 5V			1.0	μA		
V _C	Clamping Voltage	$I_{PP} = 1A, t_p = 8/20 \mu s$			9.5	V		
V _C	Clamping Voltage	$I_{PPmax} = 5A$, $t_p = 8/20 \mu s$			15.0	V		
CJ	Junction Capacitance	V _R = 0V, f = 1MHz			15	pF		

